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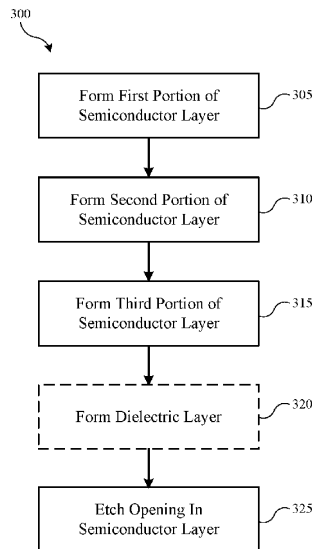


FIG. 3

(57) Abstract: Exemplary semiconductor structures and processing methods may include forming a first portion of a first semiconductor layer characterized by a first etch rate for an etch treatment, forming a second portion of the first semiconductor layer characterized by a second etch rate that is less than the first etch rate for the etch treatment, and forming a third portion of the first semiconductor layer characterized by a third etch rate that is greater than the second etch rate. The processing methods may further include etching an opening through the first semiconductor layer, where the opening has a height and a width, and where the opening is characterized by a variation in the width between a midpoint of the height of the opening and an endpoint of the opening that is less than or about 5 Å.

[Continued on next page]

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